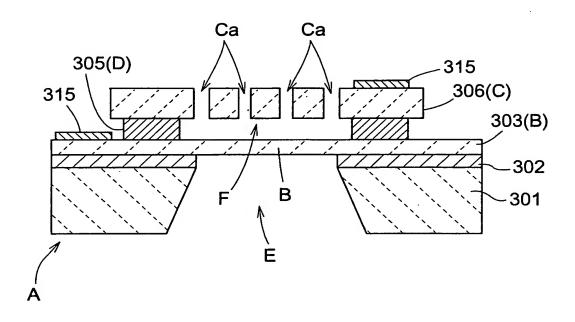
FIG.1



A: support substrate

301: monocrystal silicon substrate

B: diaphragm

302: silicon oxide film

C: back electrode

303: polycrystal silicon film

D:spacer

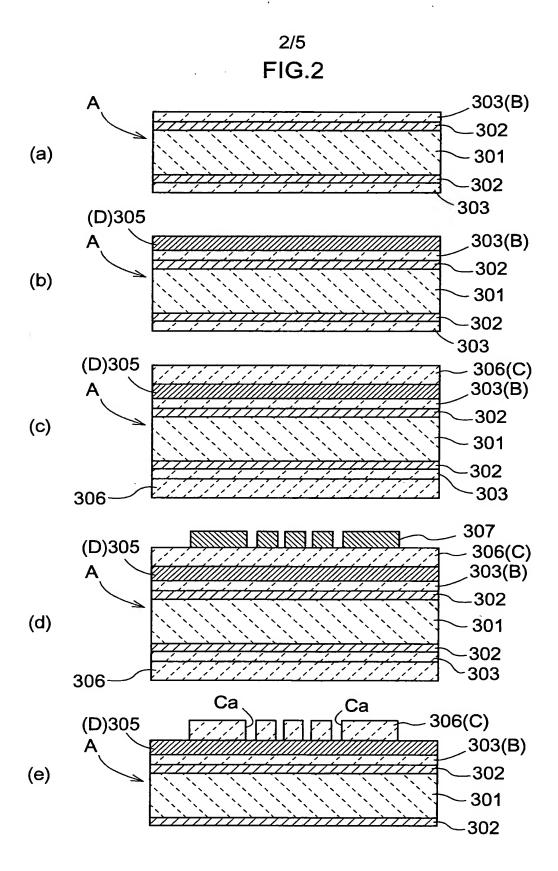
305: sacrificial layer

E: acoustic opening

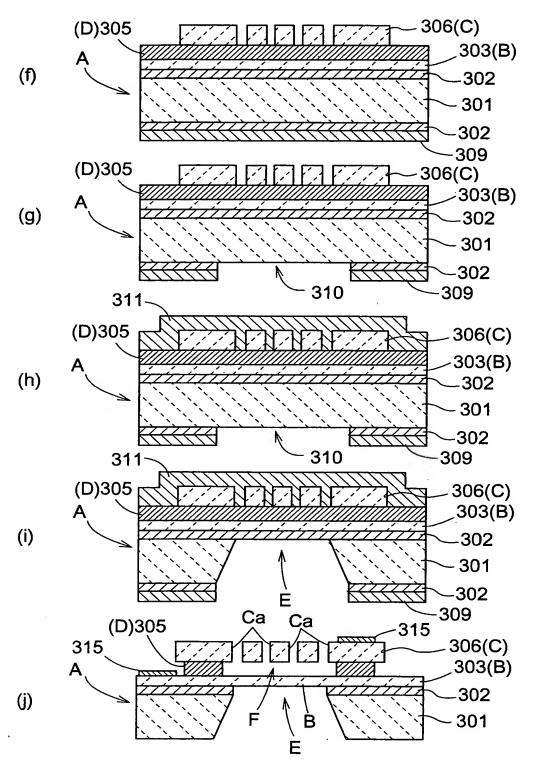
306: polycrystal silicon film

F: void area

315: take-out electrode



3/5 FIG.3



4/5

FIG.4

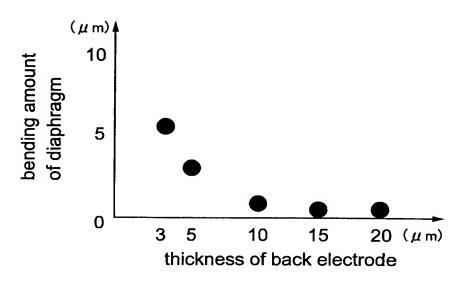


FIG.5

